2SA1179 TRANSISTOR (**PNP**)

1.BASE

2.COLLECTOR

3.EMITTER

SOT-23-3

FEATURES

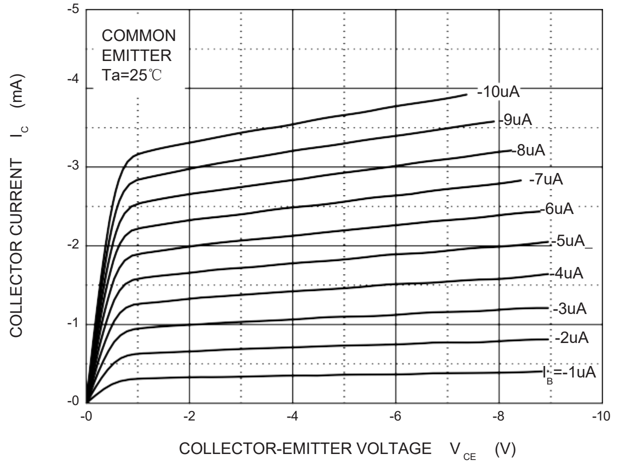
. High breakdown voltage

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

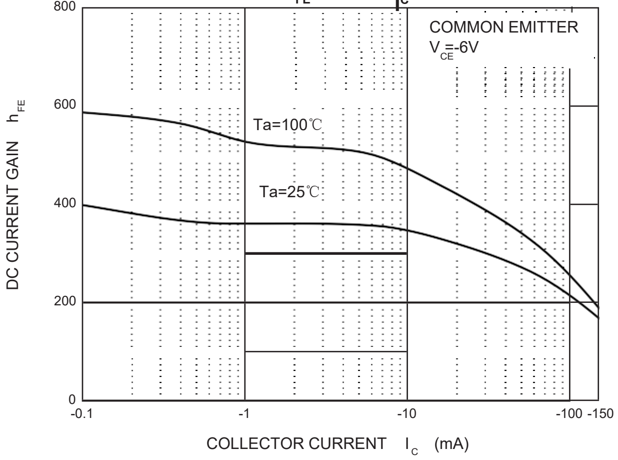
Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-55	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-150	mA
Pc	Collector Power Dissipation	200	mW
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55-150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

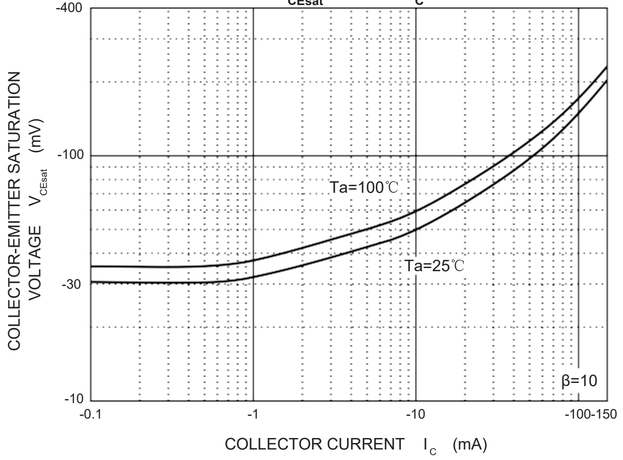
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-10u A,I_E=0	-55			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA,I_B=0	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-10 u A,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-35V,I_E=0			-0.1	u A
Emitter cut-off current	I_{EBO}	V_{EB}=-4V,I_C=0			-0.1	u A
DC current gain	h_{FE}	V_{CE}=-6V,I_C=-1mA	200		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-50mA,I_B=-5mA			-0.5	V
Base -emitter saturation voltage	$V_{BE(sat)}$	I_C=-50mA,I_B=-5mA			-1.0	V
Transition frequency	f_T	V_{CE}=-6V,I_C=-10mA		180		MHz
Collector output capacitance	C_{ob}	V_{CB}=-6V,I_E=0,f=1MHz		4		pF



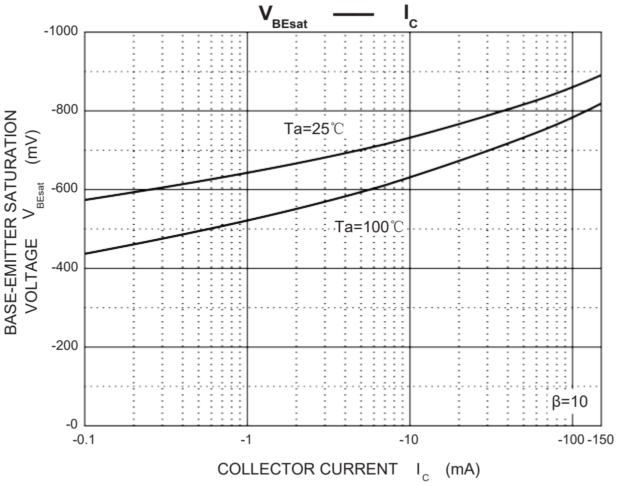
Static Characteristic



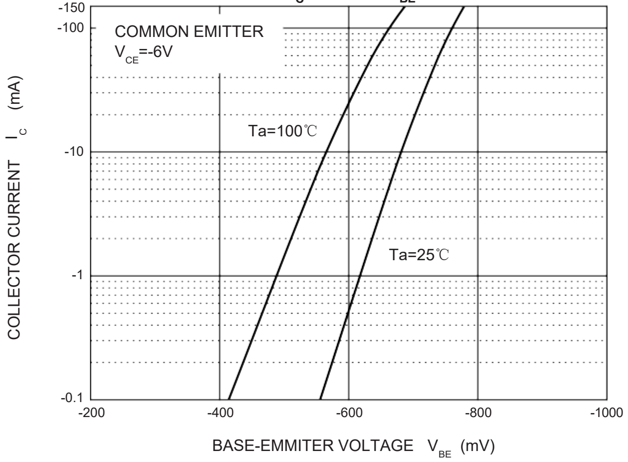
h_{FE} — I_C



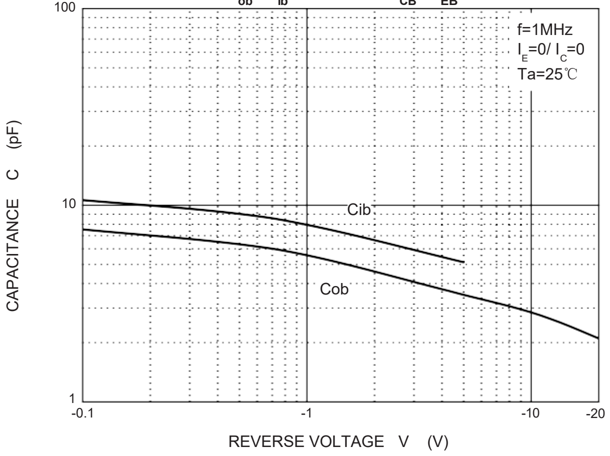
V_{CEsat} — I_C



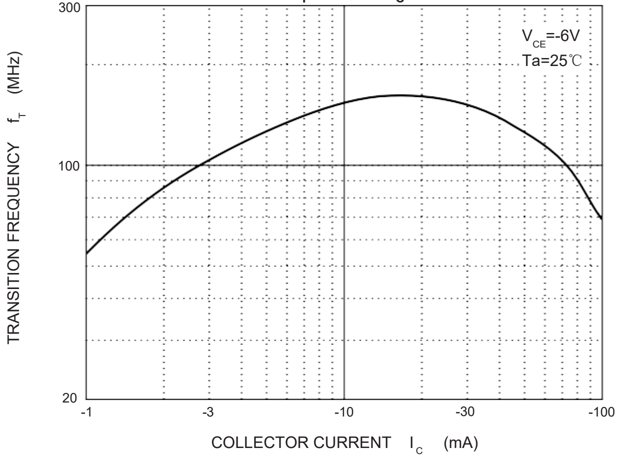
V_{BEsat} — I_C



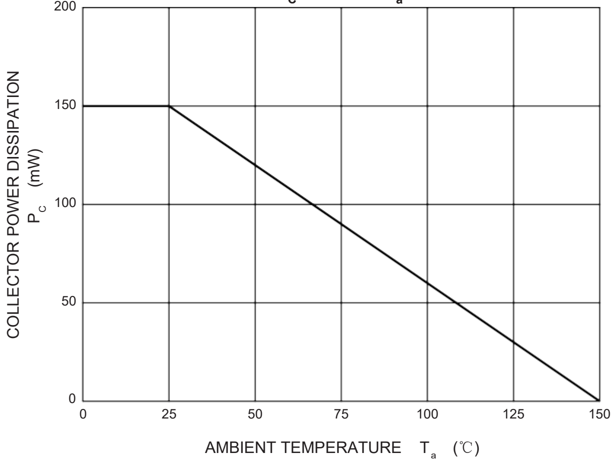
I_C — V_{BE}



C_{ob}/ C_{ib} — V_{CB}/ V_{EB}



f_T — I_C



P_C — T_a